

PATENT ABSTRACTS OF JAPAN

(11)Publication number : **02-288209**

(43)Date of publication of application : **28.11.1990**

(51)Int.Cl.

H01F 10/00

(21)Application number : **01-107567**

(71)Applicant : **AMORUFUASU DENSHI DEVICE
KENKYUSHO:KK**

(22)Date of filing : **28.04.1989**

(72)Inventor : **ONUMA SHIGEHIRO
TSUGAI NORIJI
MATSUMOTO FUMIO
HAYASHIDE MITSUO
FUJIMORI HIROYASU**

(54) MULTILAYER MAGNETIC THIN-FILM

(57)Abstract:

PURPOSE: To obtain a multilayer magnetic thin film, from which multilayer films having the stable conditions of film formation and excellent high-frequency magnetic characteristics are acquired, by using a nitride as an insulator in the multilayer magnetic thin film in which magnetic substances and the insulators are laminated alternately.

CONSTITUTION: A multilayer magnetic thin-film is manufactured by alternately laminating magnetic films and insulating layers through an evaporation method such as a sputtering method, but a material having excellent soft magnetism in a high-frequency region is required as the magnetic film, and an amorphous material having high saturation magnetic flux density, magnetostriction close to zero and high electric resistivity is proper as the material. There are metal-metal group and metal-semimetal group compositions as the amorphous material, and a Co-Nb-Zr group and a (Co.Fe)-(Si.B) group are cited as a representative composition example. A material having composite structure and composition modulation structure may be used besides said material, and any material may be employed when it is a material having excellent high-frequency characteristics in any case. The nitride of any metal or semimetal may be used as a nitride as the insulating layer, but AlN, BN, Si₃N₄, TiN and VN are particularly favorable.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of